

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-40V	8.6mΩ@-10V	-55A
	13mΩ@4.5V	

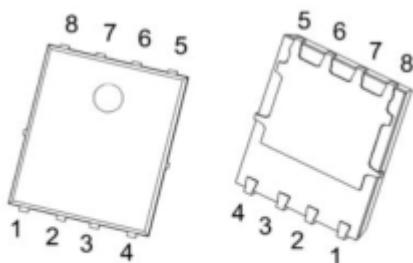
Feature

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

Applications

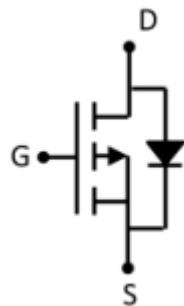
- Power switch
- Load switch in high current applications
- DC/DC converters

Package

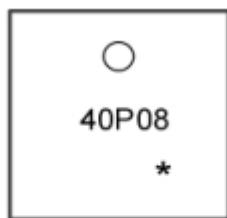


PDFN5×6-8L

Circuit diagram



Marking



40P08 : Product code
* : Month code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-55	A
Pulsed Drain Current	I_{DM}	-220	A
Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	90	W
Single pulse avalanche energy ¹	E_{AS}	700	mJ
Thermal Resistance, Junction-to-Case ²	$R_{\theta JC}$	1.39	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -40\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.2	-1.6	-2.5	V
Drain-Source On-Resistance	$R_{DS(\text{on})}$	$V_{GS} = -10\text{V}, I_D = -10\text{A}$		8.6	11	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -8\text{A}$		13	18	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		4004		pF
Output Capacitance	C_{oss}			309		
Reverse Transfer Capacitance	C_{rss}			229		
Switching Characteristics						
Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = -20\text{V}, I_D = -10\text{A}, V_{GS} = -10\text{V}, R_G = 3\Omega$		9.9		nS
Turn-on Rise Time	T_r			32		
Turn-off Delay Time	$T_{d(off)}$			46		
Turn-off Fall Time	T_f			53		
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	$V_{DS} = -20\text{V}, I_D = -20\text{A}, V_{GS} = -10\text{V}$		31		nC
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g			67		
Gate-Source Charge	Q_{gs}			13.2		
Gate-Drain Charge	Q_{gd}			11		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{V}, I_s = -60\text{A}$			-1.2	V

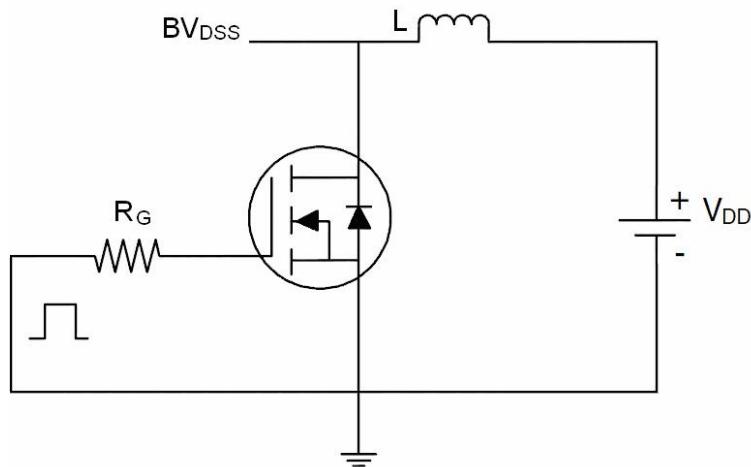
Note:

1. E_{AS} condition: $T_j = 25^\circ\text{C}, V_{DD} = -20\text{V}, V_G = -10\text{V}, L = 1\text{mH}, R_g = 25\Omega$

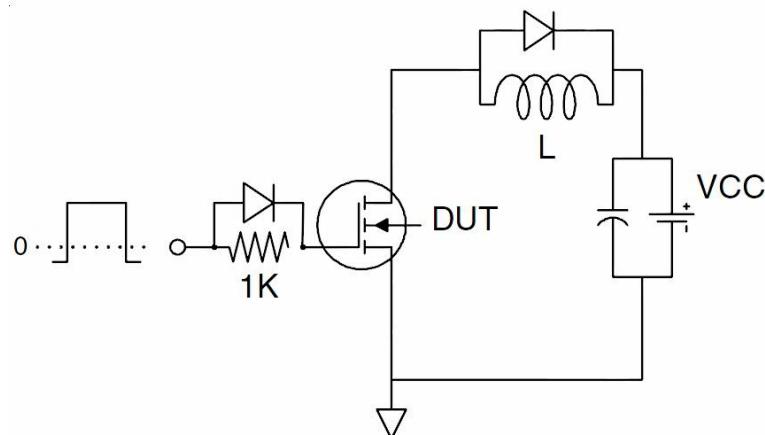
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Test Circuits

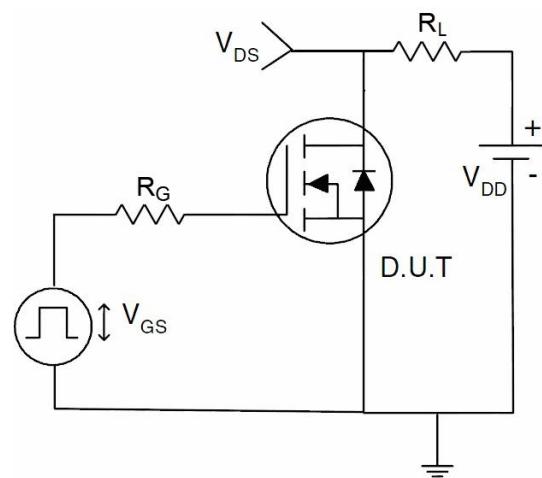
- EAS Test Circuits



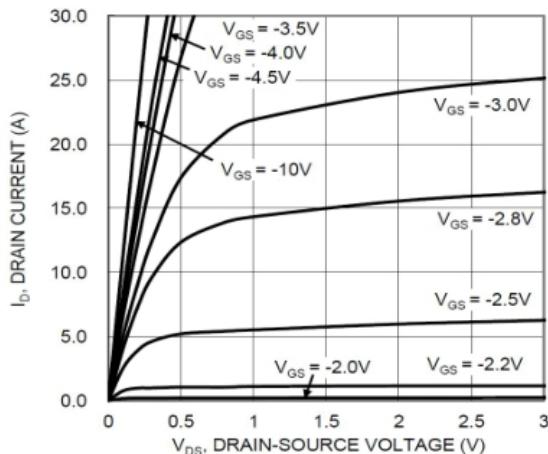
- Gate Charge Test Circuit



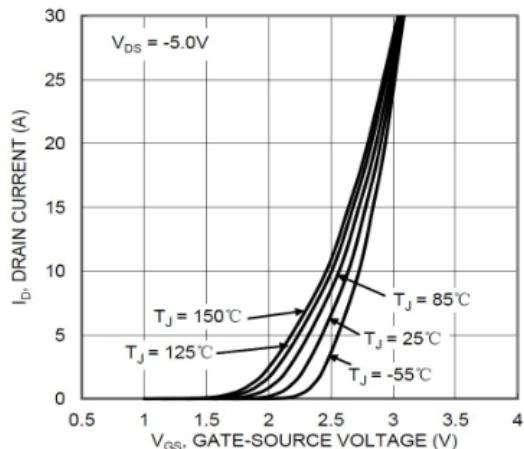
- Switch Time Test Circuit



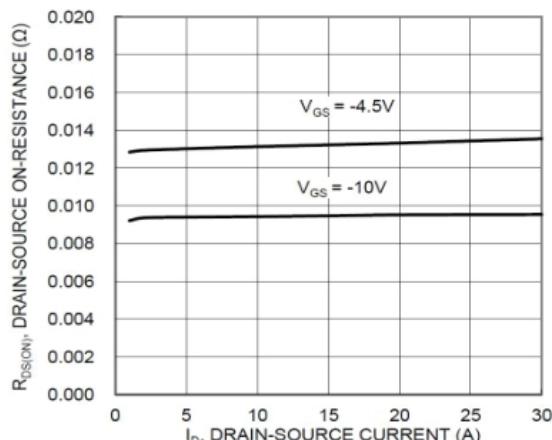
Typical Characteristics



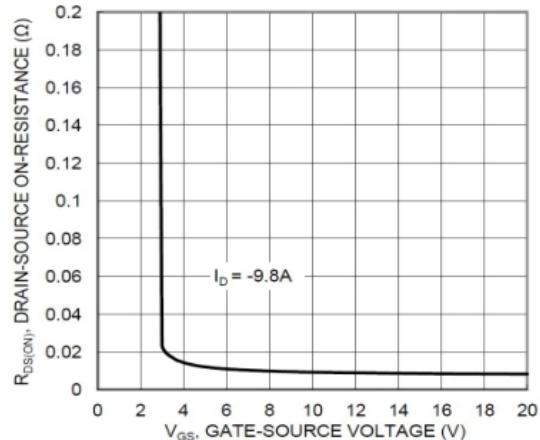
Typical Output Characteristic



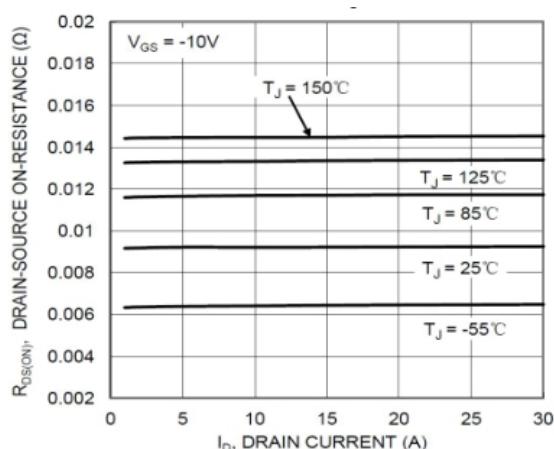
Typical Transfer Characteristic



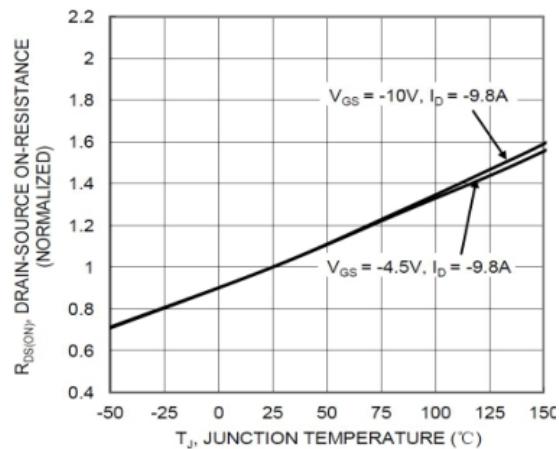
Typical On-Resistance vs. Drain Current and Gate Voltage



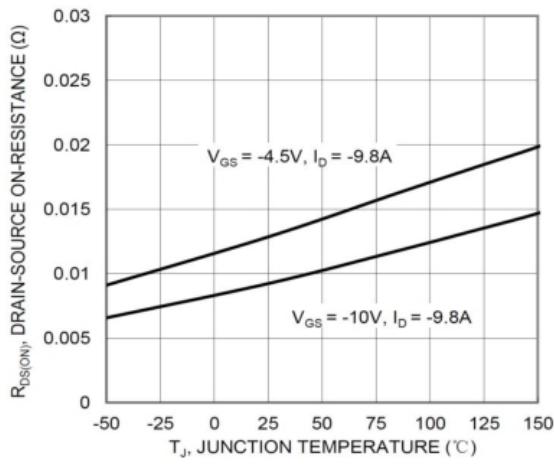
Typical Transfer Characteristic



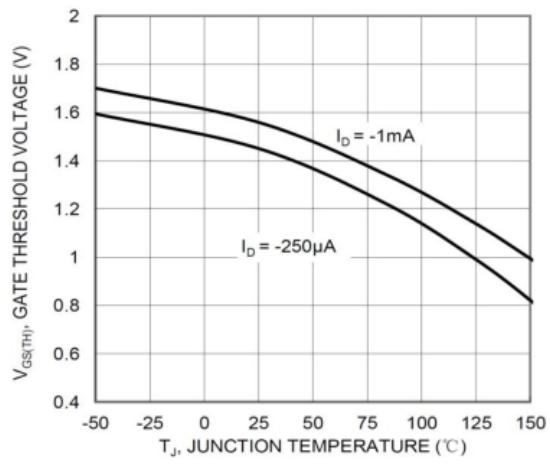
Typical On-Resistance vs. Drain Current and Temperature



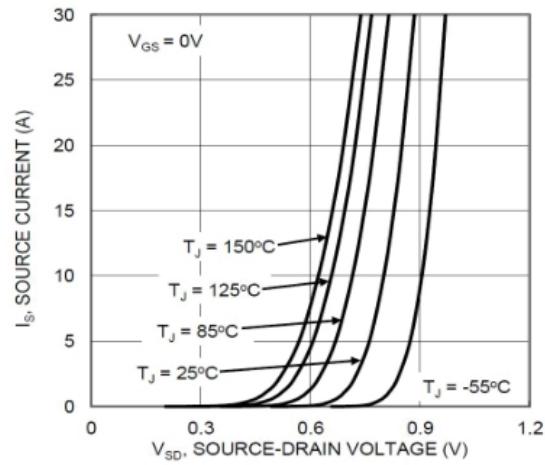
On-Resistance Variation with Temperature



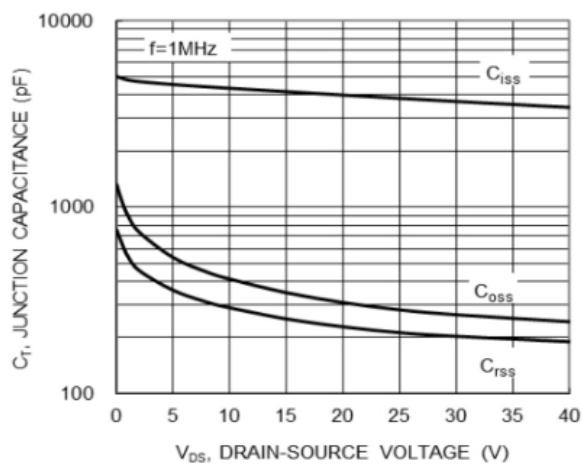
On-Resistance Variation with Temperature



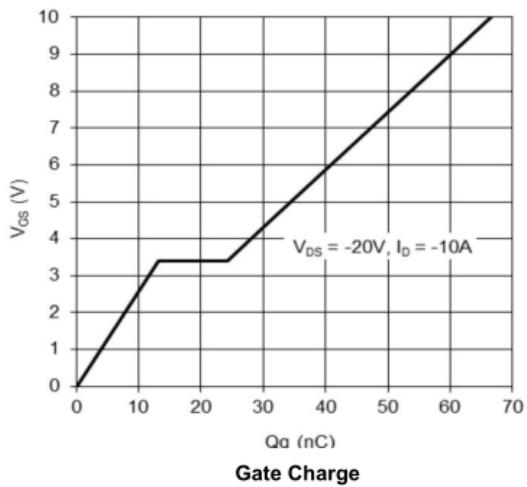
Gate Threshold Variation vs. Junction Temperature



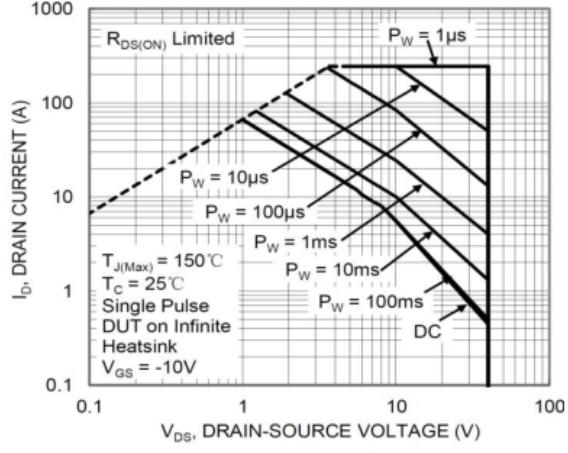
Diode Forward Voltage vs. Current



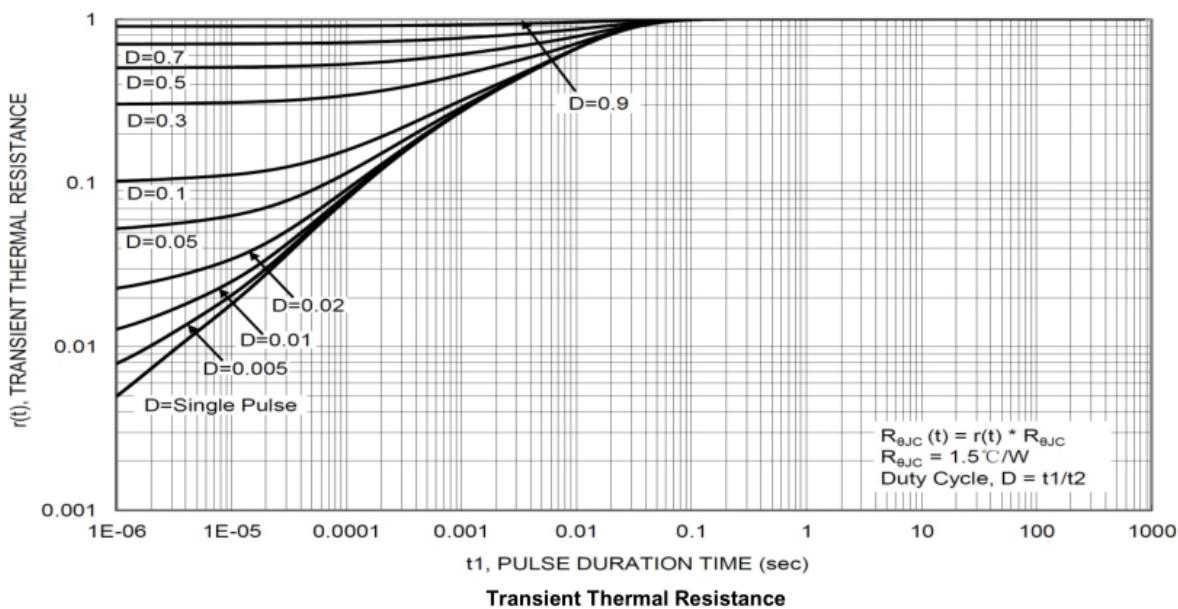
Typical Junction capacitance



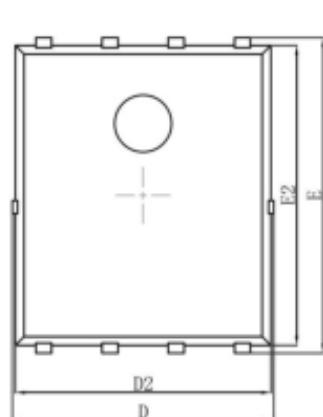
Gate Charge



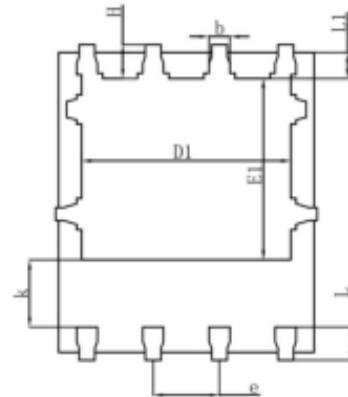
Safe Operation Area



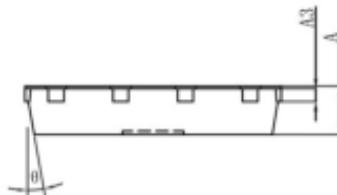
PDFN5×6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°		12°	